AMENDMENTS TO THE CLAIMS

1. (Currently amended) A method of erasing repeated patterns in a dark/light image obtained by image pickup of a subject of inspection, when identifying defects present in a repeated pattern in ~~a~~ the subject of inspection, comprising ~~the procedures of~~:

~~demarcating the obtained image into a plurality of areas;~~

detecting a reference pixel in the obtained image ~~one of said demarcated areas~~;

assigning a comparison pixel at a predetermined distance from the reference pixel, the distance being determined in accordance with the pattern pitch of the repeated patterns in the dark/light image ~~in each of the rest of said demarcated areas~~;

obtaining a plurality of density differences between said reference pixel and each of said comparison pixels;

determining a density difference that is closest to 0 as a specific density difference; and

applying said specific density difference to a reference density of the image, thereby erasing the repeated patterns in the dark/light image.

2. (Original) The method of erasing repeated patterns in a dark/light image according to Claim 1, wherein the subject of inspection is a liquid crystal array panel.

3. (Original) The method of erasing repeated patterns in a dark/light image according to Claim 1, wherein the subject of inspection is a plasma display panel.

4. (Canceled)

5. (Currently amended) The method of erasing repeated patterns in a dark/light image according to Claim 1, wherein, in the step of determining ~~a~~ the specific density difference, a mean value of the plurality of density differences between the reference pixel and the comparison pixels is determined as the specific density difference.

6. (Original) A method of manufacturing electronic equipment devices at least

including liquid crystal panels, plasma display panels, and semiconductor wafers, including an inspection process that is performed in accordance with the method of erasing repeated patterns as set forth in claim 1.

7. (Currently amended) A pattern defect inspection device comprising:

an image pickup element that picks up an image of a subject of inspection; ~~and~~

a processing device that detects pattern defects by storing and processing dark/light image data obtained by image pickup of the inspection subject, wherein the processing device ~~includes: a unit for demarcating the obtained image into a plurality of areas, detecting~~ detects a reference pixel in the obtained image ~~one of said demarcated areas~~, ~~assigning~~ assigns a comparison pixel at a predetermined distance from the reference pixel, the distance being determined in accordance with the pattern pitch of the repeated patterns in the dark/light image ~~in each of the rest of said demarcated areas~~, and ~~obtaining~~ obtains a plurality of density differences between said reference pixel and each of said comparison pixels;

a unit for determining a density difference that is closest to 0 as a specific density difference; and

a unit for applying the specific density difference to a reference density of the image and generating a pattern-erased image.

8. (Original) The pattern defect inspection device according to claim 7, wherein the subject of inspection is a liquid crystal array panel.

9. (Original) The pattern defect inspection device according to claim 7, wherein the subject of inspection is a plasma display panel.

10. (Currently amended) The pattern defect inspection device according to claim 7, wherein, instead of determining ~~a~~ the density difference that is ~~closed~~ closest to 0 as ~~a~~ the specific density difference, a mean value of the plurality of density differences between the reference pixel and the comparison pixels is determined as the specific density difference.

11. (New) The pattern defect inspection device according to claim 7, wherein the distance between the comparison pixel and the reference pixel is an integral multiple of the pattern pitch of the repeated patterns.

12. (New) The method of erasing repeated patterns in a dark/light image according to claim 1, wherein the distance between the comparison pixel and the reference pixel is an integral multiple of the pattern pitch of the repeated patterns.